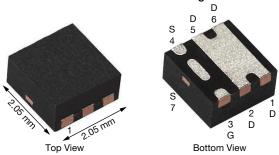
Vishay Siliconix

# P-Channel 30 V (D-S) MOSFET

# PowerPAK® SC-70-6L Single



PRODUCT SUMMARY									
V <sub>DS</sub> (V)	-30								
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = -10 \text{ V}$	0.0140								
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = -4.5 \text{ V}$	0.0241								
Q <sub>g</sub> typ. (nC)	8.9								
I <sub>D</sub> (A)	-30.3								
Configuration	Single								

Marking code: B9

#### **FEATURES**

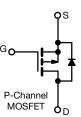
- TrenchFET® Gen IV p-channel power MOSFET
- Thermally enhanced PowerPAK® SC-70 package RoHS



- Very low R<sub>DS(on)</sub> x area minimizes power loss on limited PCB real estate
- Provides excellent R<sub>DS</sub>-Q<sub>g</sub> Figure-of-Merit (FOM) for switching applications
- 100 % Ra tested
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>

#### **APPLICATIONS**

- · Battery charging and management
- · Load switch
- DC/DC converters
- Power management in battery-operated, mobile and wearable devices



ORDERING INFORMATION	
Package	PowerPAK SC-70
Lead (Pb)-free and halogen-free	SiA471DJ-T1-GE3

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>A</sub> = 25 °C, unless otherwise noted)							
PARAMETER		SYMBOL	LIMIT	UNIT			
Drain-source voltage	$V_{DS}$	-30	V				
Gate-source voltage		$V_{GS}$	-20 / +16	v			
	T <sub>C</sub> = 25 °C		-30.3				
Continuous drain ourrent (T = 150 °C)	T <sub>C</sub> = 70 °C	Ι,	-24.2				
Continuous drain current (T <sub>J</sub> = 150 °C)	T <sub>A</sub> =25 °C	I <sub>D</sub>	-12.9 <sup>a, b</sup>				
	T <sub>A</sub> = 70 °C		-10.3 <sup>a, b</sup>	A			
Pulsed drain current (t = 100 μs)		I <sub>DM</sub>	-70				
Continuous source-drain diode current	T <sub>C</sub> = 25 °C		-16				
Continuous source-drain diode current	T <sub>A</sub> = 25 °C	l <sub>S</sub>	-2.9 <sup>a, b</sup>				
	T <sub>C</sub> = 25 °C		19.2				
Maximum navvar dissination	T <sub>C</sub> = 70 °C		12.3	w			
Maximum power dissipation	T <sub>A</sub> = 25 °C	P <sub>D</sub>	3.5 <sup>a, b</sup>	VV			
	T <sub>A</sub> = 70 °C		2.2 <sup>a, b</sup>				
Operating junction and storage temperature	range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C			
Soldering recommendations (peak temperate	ture) <sup>c, d</sup>		260	$\neg$			

THERMAL RESISTANCE RATINGS									
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT				
Maximum junction-to-ambient a, e	t ≤ 5 s	R <sub>thJA</sub>	28	36	°C/W				
Maximum junction-to-case (drain)	Steady state	R <sub>thJC</sub>	5.3	6.5	] 0///				

#### Notes

- a. Surface mounted on 1" x 1" FR4 board
- b. t = 5 s
- c. See solder profile (<a href="www.vishay.com/ppg?73257">www.vishay.com/ppg?73257</a>). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- d. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- e. Maximum under steady state conditions is 80 °C/W



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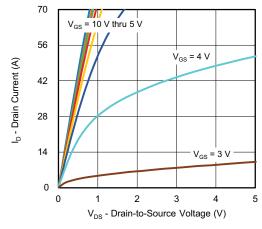
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static				•		
Drain-source breakdown voltage	$V_{DS}$	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-30	-	-	V
V <sub>DS</sub> temperature coefficient	$\Delta V_{DS}/T_{J}$	1 40 4	-	-15	-	
V <sub>GS(th)</sub> temperature coefficient	$\Delta V_{GS(th)}/T_J$	I <sub>D</sub> = -10 mA	-	5	-	mV/°C
Gate-source threshold voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-1	-	-2.5	V
Gate-source leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = -20 \text{ V} / +16 \text{ V}$	-	-	± 100	nA
Zava sata valtasa duais avuvast	I <sub>DSS</sub>	V <sub>DS</sub> = -30 V, V <sub>GS</sub> = 0 V	-	-	-1	μΑ
Zero gate voltage drain current		V <sub>DS</sub> = -30 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C	-	-	-10	
On-state drain current a	I <sub>D(on)</sub>	$V_{DS} \le -5 \text{ V}, V_{GS} = 0 \text{ V}$	-10	-	-	Α
Deline and the second	_	$V_{GS} = -10 \text{ V}, I_D = -10 \text{ A}$	-	0.0115	0.0140	-
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = -4.5 \text{ V}, I_D = -7 \text{ A}$	-	0.0185	0.0241	Ω
Forward transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -10 A	-	40	-	S
Dynamic <sup>b</sup>						
Input capacitance	C <sub>iss</sub>		-	1170	-	
Output capacitance	C <sub>oss</sub>	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	570	-	pF
Reverse transfer capacitance	C <sub>rss</sub>		-	55	-	
Total gate charge	Qg	$V_{DS} = -15 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -12 \text{ A}$	-	18.5	27.8	nC
		$V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V}, I_D = -12 \text{ A}$	-	8.9	14	
Gate-source charge	Q <sub>gs</sub>	V 45VV 45VI 40A	-	4.4	-	
Gate-drain charge	Q <sub>gd</sub>	$V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V}, I_D = -12 \text{ A}$	-	2.7	-	
Gate resistance	$R_g$	f = 1 MHz	0.22	11	22	Ω
Turn-on delay time	t <sub>d(on)</sub>		-	25	50	
Rise time	t <sub>r</sub>	$V_{DD}$ = -15 V, $R_L$ = 1.5 $\Omega$ , $I_D$ $\cong$ -10 A,	_	95	190	ns
Turn-off delay time	t <sub>d(off)</sub>	$V_{GEN}$ = -4.5 V, $R_g$ = 1 $\Omega$	-	40	80	
Fall time	t <sub>f</sub>		-	18	36	
Turn-on delay time	t <sub>d(on)</sub>		-	13	26	
Rise time	t <sub>r</sub>	$V_{DD}$ = -15 V, $R_L$ = 1.5 $\Omega$ , $I_D$ $\cong$ -10 A,	-	8	16	
Turn-off delay time	t <sub>d(off)</sub>	$V_{GEN}$ = -10 V, $R_g$ = 1 $\Omega$	_	35	70	
Fall time	t <sub>f</sub>		-	15	30	
<b>Drain-Source Body Diode Characteristic</b>	cs					
Continuous source-drain diode current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	-	-	-16	_
Pulse diode forward current	I <sub>SM</sub>		-	-	-70	Α
Body diode voltage	$V_{SD}$	$I_S = -10 \text{ A}, V_{GS} = 0 \text{ V}$	-	-0.85	-1.2	V
Body diode reverse recovery time	t <sub>rr</sub>		-	21	42	ns
Body diode reverse recovery charge	Q <sub>rr</sub>	I <sub>F</sub> = -10 A, di/dt = 100 A/µs,	-	8	16	nC
Reverse recovery fall time	T <sub>J</sub> = 25 °C	-	9	-		
Reverse recovery rise time	t <sub>a</sub>		_	12	_	ns

#### Notes

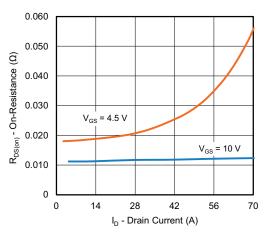
- a. Pulse test; pulse width  $\leq 300~\mu\text{s},$  duty cycle  $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

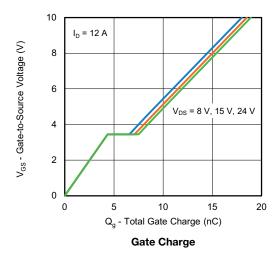


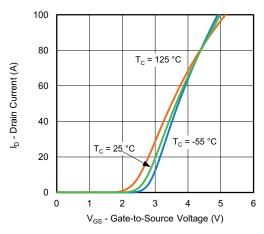


#### **Output Characteristics**

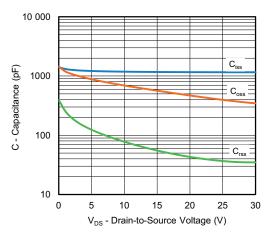


On-Resistance vs. Drain Current and Gate Voltage

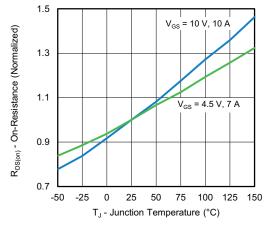




**Transfer Characteristics** 

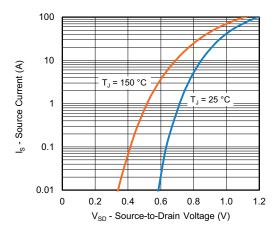


Capacitance

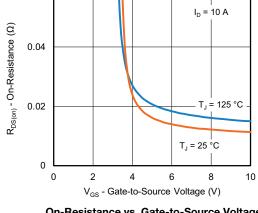


On-Resistance vs. Junction Temperature



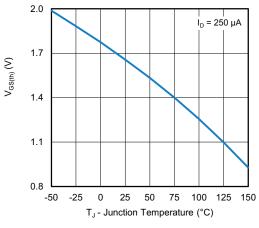


Source-Drain Diode Forward Voltage

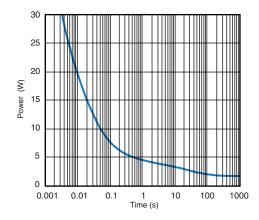


0.06

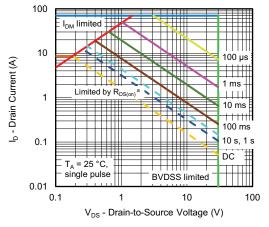
On-Resistance vs. Gate-to-Source Voltage



**Threshold Voltage** 



Single Pulse Power, Junction-to-Ambient

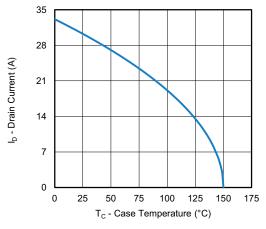


Safe Operating Area, Junction-to-Ambient

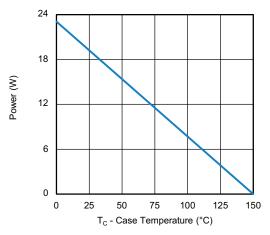
# Note

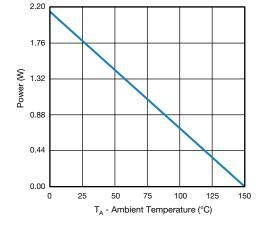
a.  $V_{GS}$  > minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified





#### Current Derating a





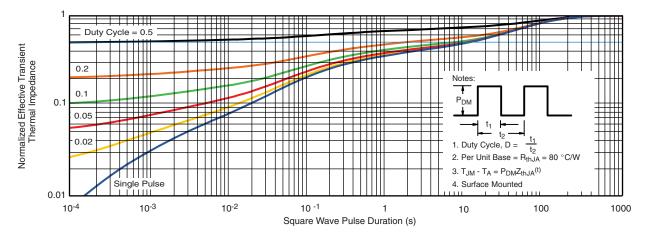
Power, Junction-to-Case

Power, Junction-to-Ambient

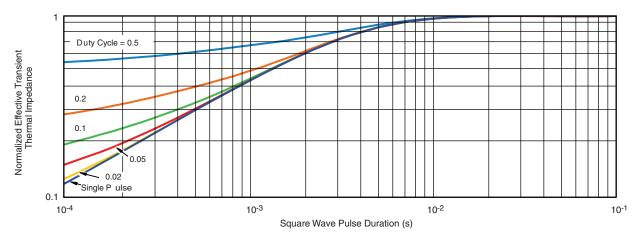
#### Note

a. The power dissipation P<sub>D</sub> is based on T<sub>J</sub> max. = 150 °C, using junction-to-ambient thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit





#### Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

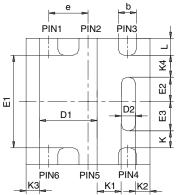
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?76741">www.vishay.com/ppg?76741</a>.





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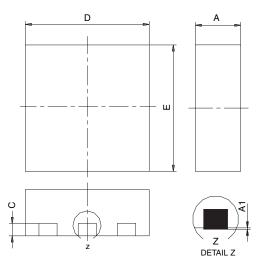
# PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
  Package outline exclusive of mold flash and metal burr
  Package outline inclusive of plating

	SINGLE PAD						DUAL PAD					
DIM	MILLIMETERS			INCHES			MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028
D2	0.135	0.235	0.335	0.005	0.009	0.013						
Е	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041
E2	0.345	0.395	0.445	0.014	0.016	0.018						
E3	0.425	0.475	0.525	0.017	0.019	0.021						
е		0.65 BSC			0.026 BSC	;	0.65 BSC			0.026 BSC		
K		0.275 TYP			0.011 TYP		0.275 TYP			0.011 TYP		
K1		0.400 TYP			0.016 TYP		0.320 TYP			0.013 TYP		
K2		0.240 TYP		0.009 TYP		0.252 TYP			0.010 TYP			
К3		0.225 TYP		0.009 TYP						•	•	
K4		0.355 TYP			0.014 TYP							
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015
T							0.05	0.10	0.15	0.002	0.004	0.006

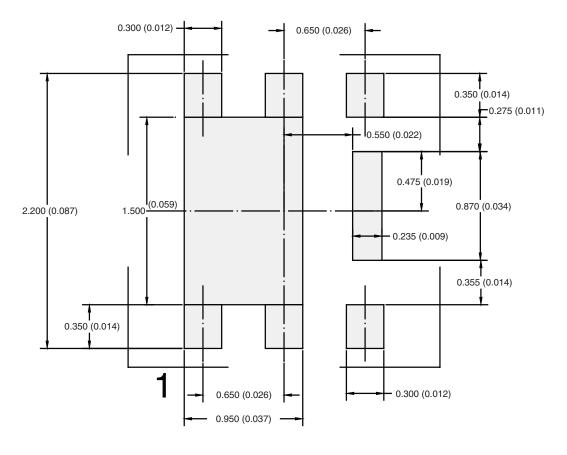
ECN: C-07431 - Rev. C, 06-Aug-07

DWG: 5934

06-Aug-07



# RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Single



Dimensions in mm/(Inches)

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ATTLICATION NOT



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Vishay

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